

N-CHANNEL SILICON POWER MOSFET



FUJI POWER MOSFET Super FAP-G Series

■ Features

High speed switching	Low on-resistance
No secondary breakdown	Low driving power
Avalanche-proof	

■ Applications

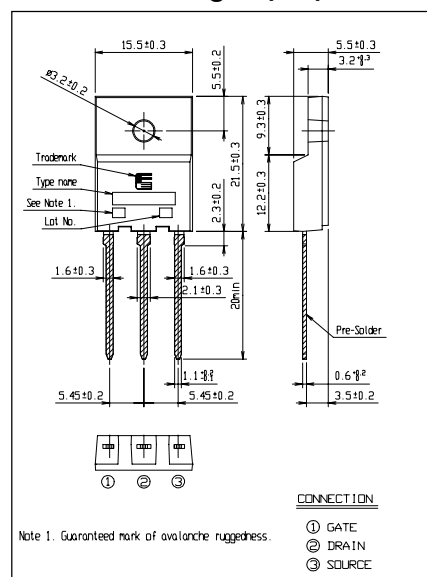
Switching regulators DC-DC converters
UPS (Uninterruptible Power Supply)

■ Maximum ratings and characteristic

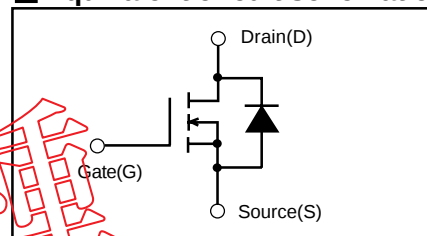
- Absolute maximum ratings
(Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V _{DS}	200	V	V _{GS} =-30V
	V _{DSX}	200	V	
Continuous Drain Current	I _D	73	A	
Pulsed Drain Current	I _D (puls)	±292	A	
Gate-Source Voltage	V _{GS}	±30	V	
Maximum Avalanche current	I _{AR}	73	A	Note *1
Non-Repetitive	E _{AS}	1152	mJ	Note *2
Maximum Avalanche Energy	E _{AR}	41	mJ	Note *3
Repetitive				
Maximum Avalanche Energy				
Maximum Drain-Source dV/dt	dV _{DS} /dt	20	kV/μs	V _{DS} ≤200V
Peak Diode Recovery dV/dt	dV/dt	5	kV/μs	Note *4
Max. Power Dissipation	P _D	210	W	T _C =25°C
		313		T _a =25°C
Operating and Storage	T _{env}	+150	°C	
Temperature range	T _{stg}	-55 to +150	°C	

■ **Outline Drawings** (mm) 200406



■ Equivalent circuit schematic



Note *1: $T_{ch} \leq 150^{\circ}\text{C}$, Repetitive and Non-repetitive

Note *2: Starting Tch=25°C. I_{AS}=30A. L=1.98mH.

$V_{DD}=48V, R_G=50\Omega$

EAS limited by maximum channel temperature
and Avalanche current.

See to the 'Avalanche Energy' graph

Note *3: Repetitive rating: Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal impedance' graph.

● Electrical characteristics (T_c =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA V _{GS} =0V	200			V
Gate Threshold Voltage	V _{GS(th)}	I _D = 250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V V _{GS} =0V T _{ch} =25°C			25	μA
		V _{DS} =160V V _{GS} =0V T _{ch} =125°C			250	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V V _{DS} =0V			100	nA
Drain-Source On-State Resistance	R _{DS(on)}	I _D =36.5A V _{GS} =10V		29	36	mΩ
Forward Transconductance	g _{fs}	I _D =36.5A V _{DS} =25V	12	24		S
Input Capacitance	C _{iss}	V _{DS} =75V		3800	5400	pF
Output Capacitance	C _{oss}	V _{GS} =0V		530	795	
Reverse Transfer Capacitance	C _{rss}	f=1MHz		35	52.5	
Turn-On Time t _{on}	t _{d(on)}	V _{CC} =48V I _D =36.5A		40	60	ns
	t _r	V _{GS} =10V		94	141	
Turn-Off Time t _{off}	t _{d(off)}	R _{GS} =10 Ω		60	90	
	t _f			30	45	
Total Gate Charge	Q _G	V _{CC} =100V		80	120	nC
Gate-Source Charge	Q _{GS}	I _D =73A		30	45	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		25	38	
Diode forward on-voltage	V _{SD}	I _F =73A V _{GS} =0V T _{ch} =25°C		1.20	1.50	V
Reverse recovery time	t _{rr}	I _F =73A V _{GS} =0V		300		ns
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		3.0		μC

- **Thermal characteristics**

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			0.595	°C/W
	R _{th(ch-a)}	channel to ambient			40.0	°C/W

Characteristics

